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[Continued on next page]

(54) **Title**: METHODS AND SYSTEMS FOR PREVENTING FEATURE COLLAPSE DURING MICROELECTRONIC TOPOGRAPHY FABRICATION

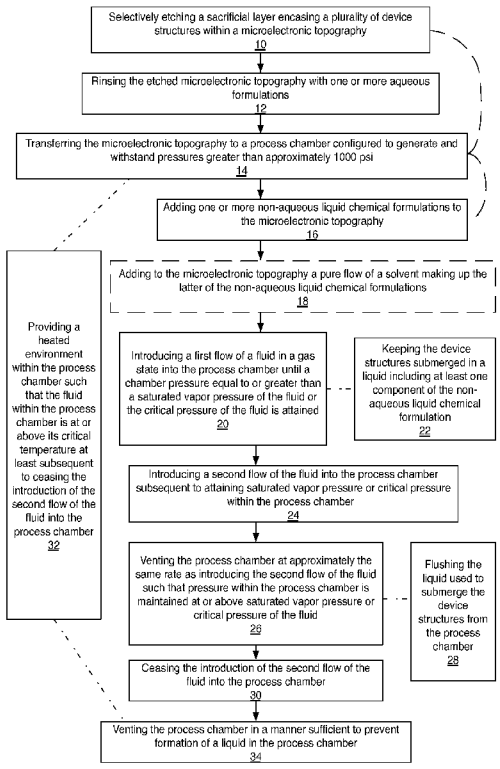


FIG. 1

(57) **Abstract**: Methods and systems for preventing feature collapse subsequent to etching include adding a rinse liquid to a microelectronic topography having remnants of another rinse liquid arranged upon its surface and subsequently exposing the topography to a pressurized chamber including a fluid at or greater than critical pressure. The methods include flushing from the pressurized chamber liquid arranged upon the topography and, thereafter, venting the chamber in a manner sufficient to prevent liquid formation therein.

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